

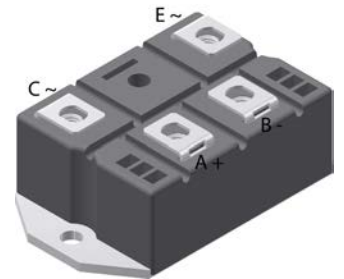
Standard Rectifier Module

1~ Rectifier
$V_{RRM} = 1600\text{ V}$
$I_{DAV} = 160\text{ A}$
$I_{FSM} = 2800\text{ A}$

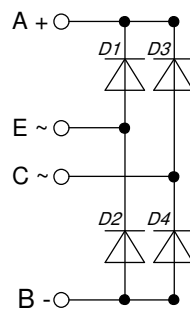
1~ Rectifier Bridge

Part number

VBO160-16NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For one phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-E

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

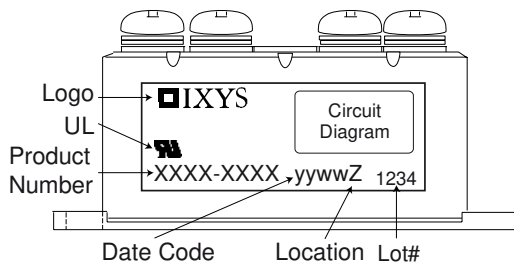
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1700	V
V_{RRM}	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1600	V
I_R	reverse current	$V_R = 1600 V$		$T_{VJ} = 25^{\circ}C$		200	μA
		$V_R = 1600 V$		$T_{VJ} = 150^{\circ}C$		3,5	mA
V_F	forward voltage drop	$I_F = 160 A$		$T_{VJ} = 25^{\circ}C$		1,07	V
		$I_F = 320 A$				1,22	V
		$I_F = 160 A$		$T_{VJ} = 125^{\circ}C$		0,96	V
		$I_F = 320 A$				1,15	V
I_{DAV}	bridge output current	$T_C = 110^{\circ}C$		$T_{VJ} = 150^{\circ}C$		160	A
		rectangular	d = 0.5				
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}C$		0,74	V
r_F	slope resistance					2,4	m Ω
R_{thJC}	thermal resistance junction to case					0,4	K/W
R_{thCH}	thermal resistance case to heatsink				0,15		K/W
P_{tot}	total power dissipation			$T_C = 25^{\circ}C$		310	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		2,80	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0 V$		3,03	kA
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		2,38	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0 V$		2,57	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		39,2	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0 V$		38,1	kA ² s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		28,3	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0 V$		27,5	kA ² s
C_J	junction capacitance	$V_R = 400 V; f = 1 MHz$		$T_{VJ} = 25^{\circ}C$		133	pF



Package PWS-E		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			250	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				273		g
M_D	mounting torque		4,25		5,75	Nm
M_T	terminal torque		4,25		5,75	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	12,0			mm
$d_{Spb/Apb}$		terminal to backside	26,0			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

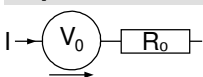


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBO160-16NO7	VBO160-16NO7	Box	5	491381

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

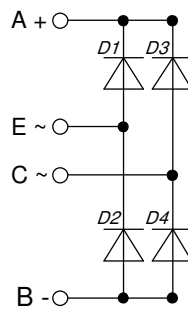
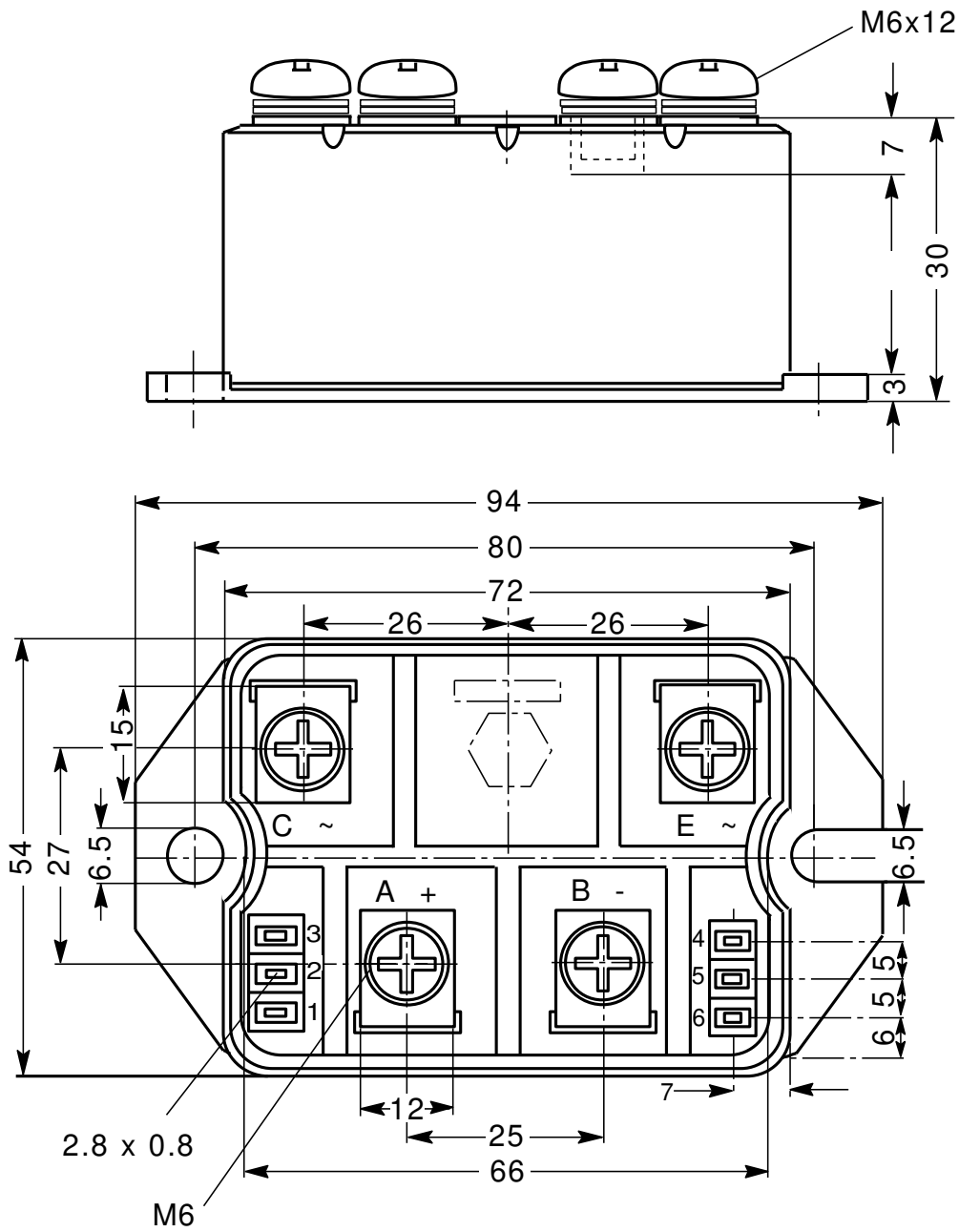


Rectifier

$V_{0\ max}$	threshold voltage	0,74	V
$R_{0\ max}$	slope resistance *	1,2	mΩ



Outlines PWS-E





Rectifier

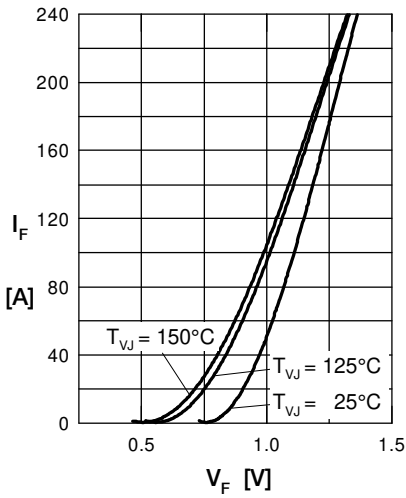


Fig. 1 Forward current vs. voltage drop per diode

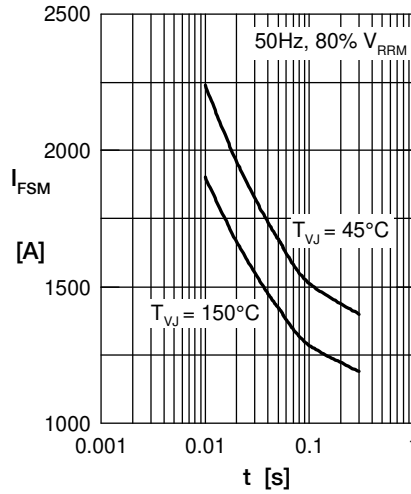


Fig. 2 Surge overload current vs. time per diode

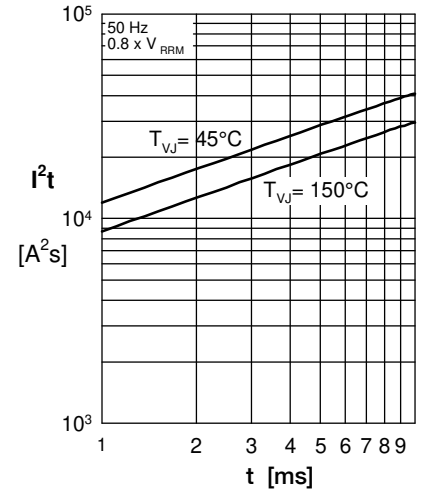


Fig. 3 I^2t vs. time per diode

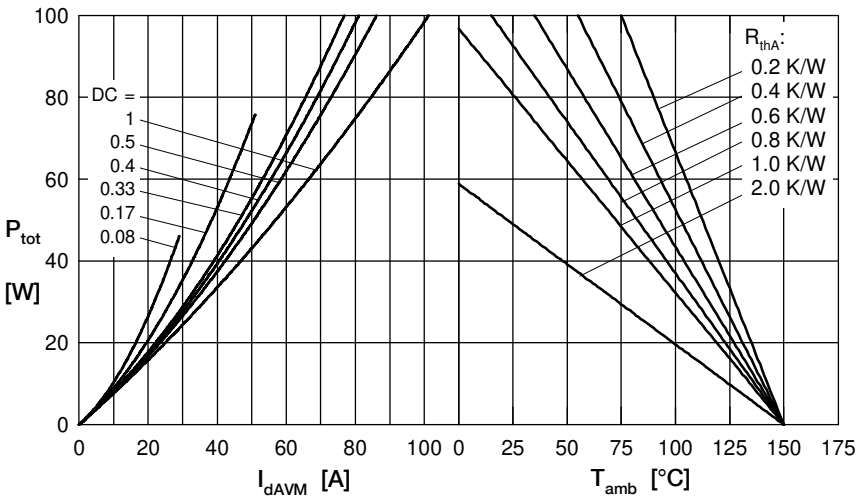


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

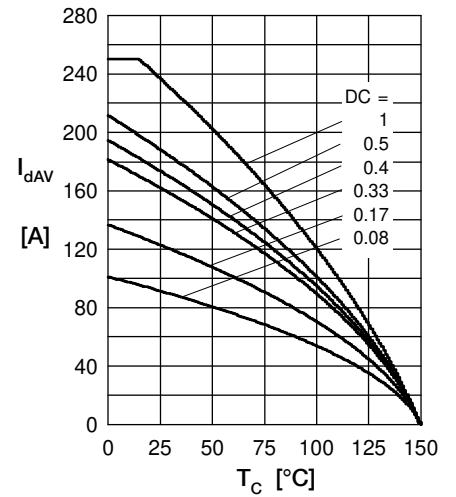


Fig. 5 Max. forward current vs. case temperature per diode

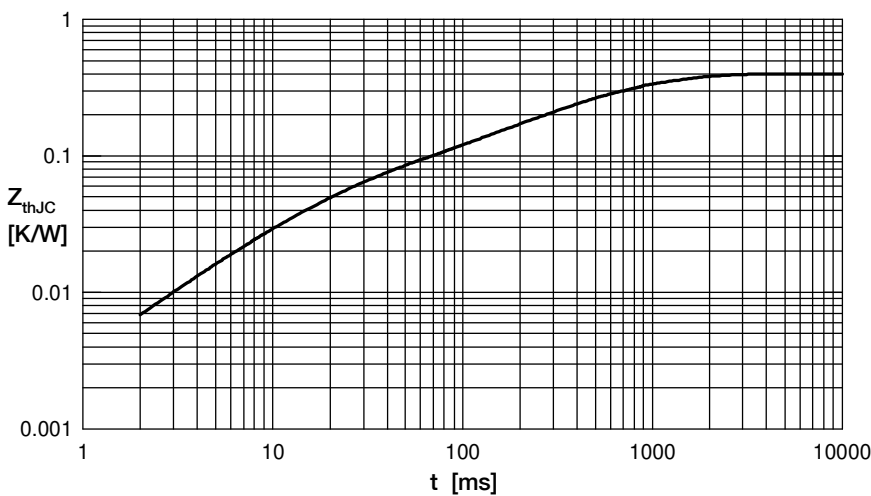


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.050	0.02
0.003	0.01
0.100	0.225
0.177	0.8
0.070	0.58